

SN74AHCT1G00 シングル 2 入力、正論理 NAND ゲート

1 特長

- 動作範囲 : 4.5V ~ 5.5V
- 最大 t_{pd} : 7.1ns (5V 時)
- 低消費電力、最大 I_{CC} 10 μ A
- ± 8 mA の出力駆動能力 (5V 時)
- 入力は TTL 電圧互換
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- IP 電話
- ノート PC
- プリンタ
- アクセス制御とセキュリティ
- 太陽光インバータ

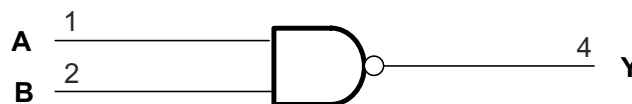
3 概要

SN74AHCT1G00 デバイスは、ブール関数 $Y = \overline{A \times B}$ 、つまり $Y = \overline{A + B}$ を正論理で実行します。

パッケージ情報

部品番号	パッケージ ¹	パッケージ・サイズ ²
SN74AHCT1G00	DBV (SOT-23、5)	2.8mm × 2.8mm
	DCK (SC-70、5)	2.00mm × 1.25mm

- 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。



論理図 (正論理)



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4 Pin Configuration and Functions

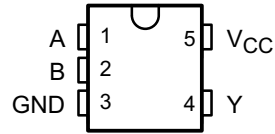


図 4-1. DBV or DCK Package 5-PIN SOT-23 OR SC-70 (Top View)

表 4-1. Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	A	I	Input A
2	B	I	Input B
3	GND	—	Ground Pin
4	Y	O	Output Y
5	V _{CC}	—	Power Pin

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
V _I	Input voltage ⁽²⁾	-0.5	7	V
V _O	Output voltage ⁽²⁾	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-20 mA
I _{OK}	Output clamp current	V _O < 0 or V _O > V _{CC}		-20 mA
I _O	Continuous output current	V _O = 0 to V _{CC}		-25 mA
	Continuous current through V _{CC} or GND	-50	50	mA
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	2		V
V _{IL}	Low-level Input voltage		0.8	V
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current		-8	mA
I _{OL}	Low-level output current		8	mA
Δt/Δv	Input transition rise or fall rate		20	ns/V
T _A	Operating free-air temperature	-40	125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74AHCT1G00		UNIT
		DBV (SOT-23)	DCK (SC-70)	
		5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	278	289.2	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	180.5	205.8	
R _{θJB}	Junction-to-board thermal resistance	184.4	176.2	
ψ _{JT}	Junction-to-top characterization parameter	115.4	117.6	
ψ _{JB}	Junction-to-board characterization parameter	183.4	175.1	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	I _{OH} = –50 μA	4.5 V	4.4	4.5		4.4		4.4	V	
	I _{OH} = –8 mA		3.94		3.8		3.8			
V _{OL}	I _{OL} = 50 μA	4.5 V			0.1		0.1	0.1	V	
	I _{OL} = 8 mA			0.36		0.44	0.44			
I _I	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	±1	μA	
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V			1		10	10	μA	
ΔI _{CC} ⁽¹⁾	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5	1.5	mA	
C _i	V _I = V _{CC} or GND	5 V		2	10		10	10	pF	

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

5.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see [Load Circuits and Voltage Waveforms](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C		–40°C to 85°C		–40°C to 125°C		UNIT
				TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	A or B	Y	C _L = 15 pF	5	6.2	1	7.1	1	8	ns
t _{PHL}				5	6.2	1	7.1	1	8	
t _{PLH}	A or B	Y	C _L = 15 pF	5.5	7.9	1	9	1	10	ns
t _{PHL}				5.5	7.9	1	9	1	10	

5.7 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd}	No load, f = 1 MHz	10.5	pF

5.8 Typical Characteristics

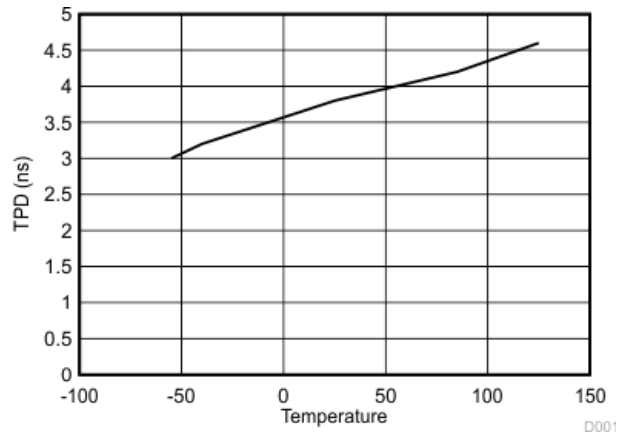
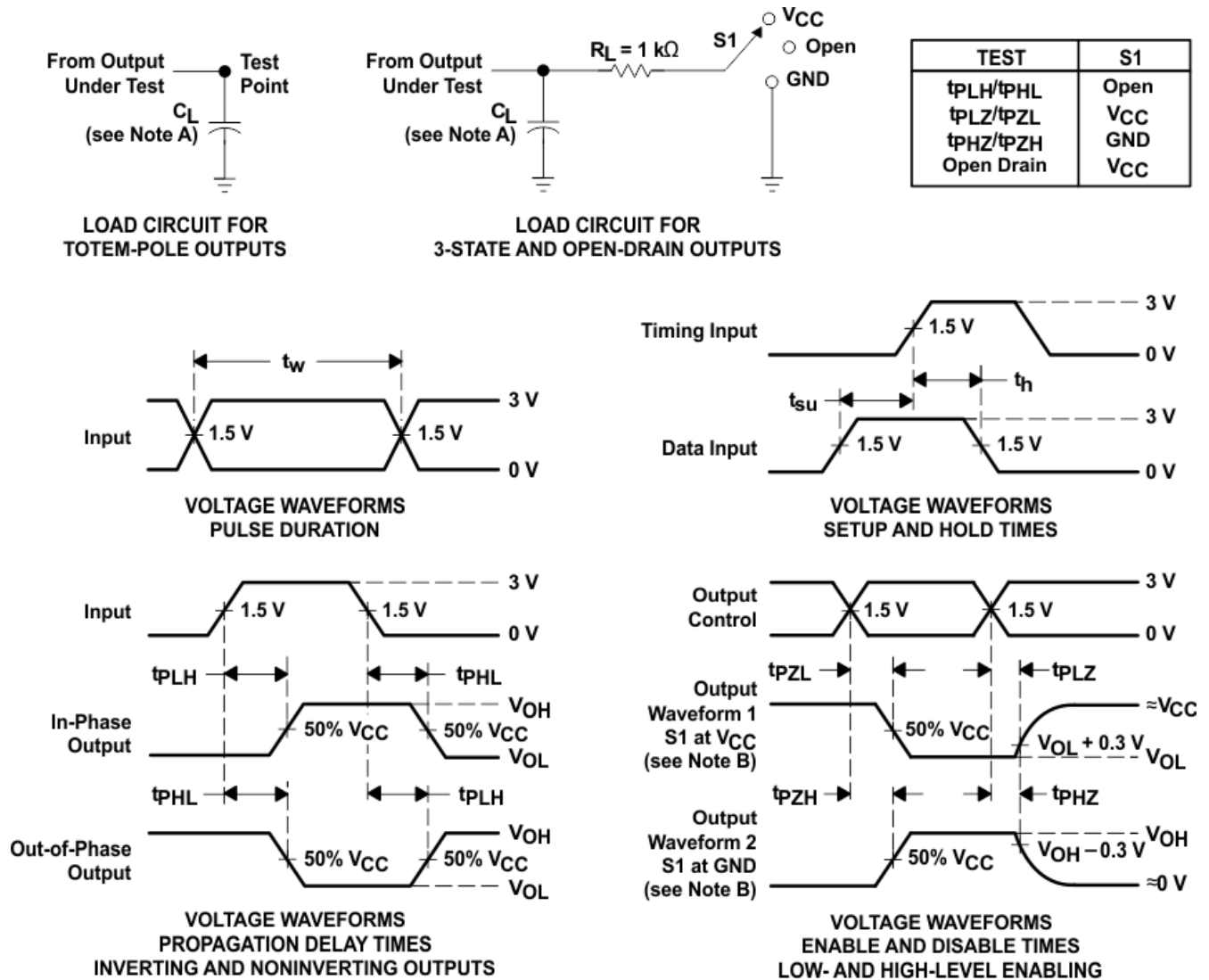


図 5-1. TPD vs Temperature

6 Parameter Measurement Information



- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 1\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
 D. The outputs are measured one at a time with one input transition per measurement.
 E. All parameters and waveforms are not applicable to all devices.

图 6-1. Load Circuits and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHCT1G00 device performs the Boolean function $Y = \overline{A \times B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The device has TTL inputs that allow up translation from 3.3 V to 5 V. The inputs are high impedance when $V_{CC} = 0$ V.

7.2 Functional Block Diagram

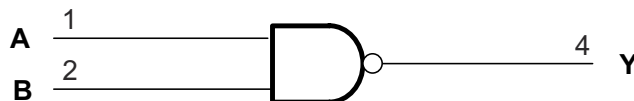


図 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

The device is ideal for operating in a 5-V logic system. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low power consumption makes this device a good choice for portable and battery power-sensitive applications.

7.4 Device Functional Modes

表 7-1. Function Table

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The SN74AHCT1G00 is a low drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The TTL inputs can accept voltages down to 3.3 V and translate up to 5 V.

8.2 Typical Application

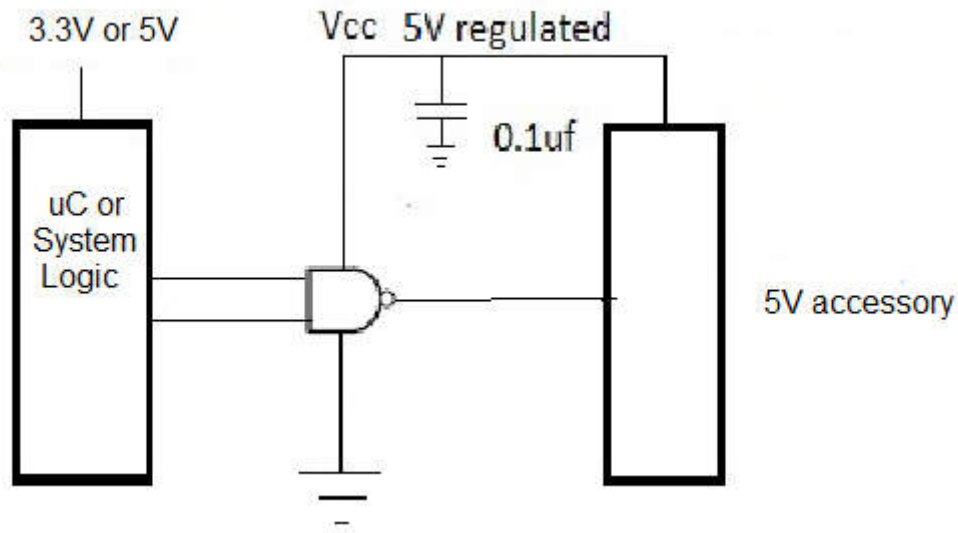


図 8-1. Typical Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so consider routing and load conditions to prevent ringing.

8.3 Detailed Design Procedure

- Recommended input conditions:
 - Specified high and low levels. See (V_{IH} and V_{IL}) in [セクション 5.3](#).
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC} .
- Recommended output conditions:
 - Load currents should not exceed 25 mA per output and 50 mA total for the part.
 - Outputs should not be pulled above V_{CC} .

8.4 Application Curves

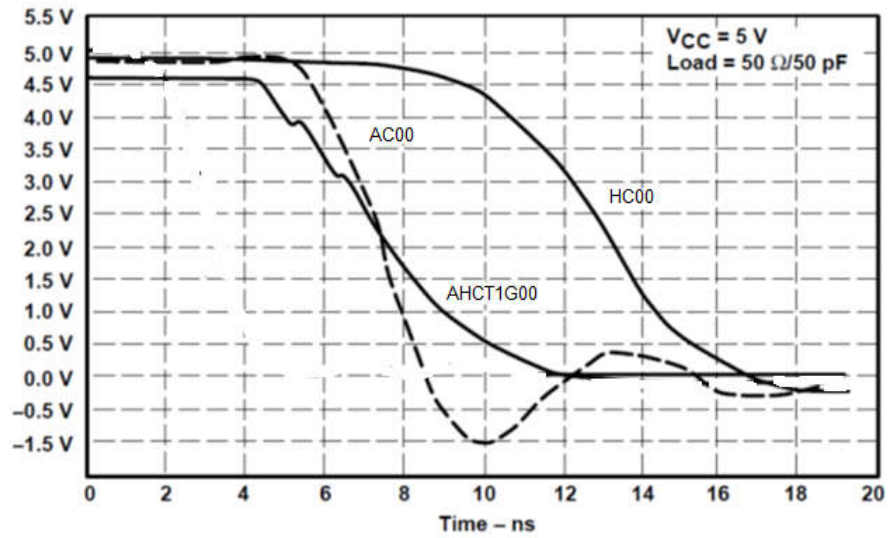


図 8-2. Switching Characteristics Comparison

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](#) のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
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9.5 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

Changes from Revision O (October 2023) to Revision P (February 2024) Page

- Updated thermal values for DBV package from R θ JA = 208.2 to 278, R θ JC(top) = 76.1 to 180.5, R θ JB = 52.5 to 184.4, Ψ JT = 4 to 115.4, Ψ JB = 51.8 to 183.4, R θ JC(bot) = N/A, all values in °C/W **5**

Changes from Revision N (March 2015) to Revision O (October 2023) Page

- 「パッケージ情報」表にパッケージ・サイズを追加 **1**
- Updated thermal values for DCK package from R θ JA = 287.6 to 289.2, R θ JC(top) = 97.7 to 205.8, R θ JB = 65 to 176.2, Ψ JT = 2 to 117.6, Ψ JB = 64.2 to 175.1, R θ JC(bot) = N/A, all values in °C/W **5**

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
74AHCT1G00DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	B00G	Samples
74AHCT1G00DBVTG4	OBSOLETE	SOT-23	DBV	5		TBD	Call TI	Call TI	-40 to 125	B00G	
74AHCT1G00DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	BA3	Samples
74AHCT1G00DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	BA3	Samples
74AHCT1G00DCKTG4	OBSOLETE	SC70	DCK	5		TBD	Call TI	Call TI	-40 to 125	BA3	
SN74AHCT1G00DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(37UH, B003, B00G, B00J, B00S)	Samples
SN74AHCT1G00DBVT	OBSOLETE	SOT-23	DBV	5		TBD	Call TI	Call TI	-40 to 125	(B003, B00G, B00J, B00S)	
SN74AHCT1G00DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 85	BAY	Samples
SN74AHCT1G00DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	(1QO, BA3, BAG, BA J, BAS)	Samples
SN74AHCT1G00DCKT	OBSOLETE	SC70	DCK	5		TBD	Call TI	Call TI	-40 to 125	(BA3, BAG, BAJ, BA S)	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AHCT1G00 :

- Automotive : [SN74AHCT1G00-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74AHCT1G00DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
74AHCT1G00DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHCT1G00DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHCT1G00DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHCT1G00DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74AHCT1G00DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
74AHCT1G00DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHCT1G00DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74AHCT1G00DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHCT1G00DCKR	SC70	DCK	5	3000	210.0	185.0	35.0

DCK0005A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

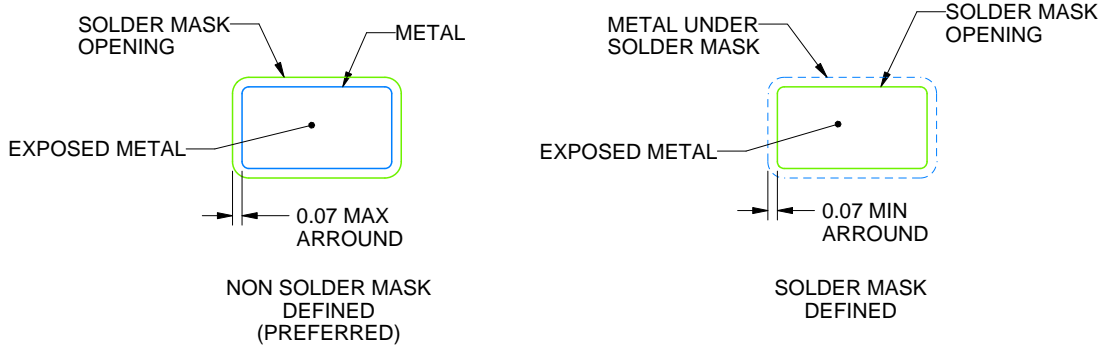
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE: 18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214839/K 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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